NSN 5962-01-369-9251

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Maximum Power Dissipation Rating:
880.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
An/fps-124
Features Provided:
Programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
9 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
-30.00 milliamperes collector cutoff current, dc, with specified resistance between base and emitter microamperes and 5.00 milliampere
reverse current, dc microamperes
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, schottky, bipolar 4096bit prom, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 7.0 volts total supply
Time Rating Per Chacteristic:
45.00 nanoseconds af output megawatts
Memory Device Type:
Prom
Hybrid Technology Type:
Monolithic
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification

format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

standard (includes industry or association standards, individual manufactureer standards, etc.).

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883

Terminal Type And Quantity:

20 printed circuit

Specification Data:

56232-1219251 manufacturers specification

Specification Or Standard:

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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